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Correction: An ion-gating synaptic memristor based on tri-layer HfO_x composition regulation

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Correction for 'An ion-gating synaptic memristor based on tri-layer HfO_x composition regulation' by Lanqing Zou *et al.*, *J. Mater. Chem. C*, 2025, **13**, 5326–5331, <https://doi.org/10.1039/D4TC04564E>.

The authors regret that an incorrect version of Fig. 4a was included in the published article, showing incorrect data points for the first cycle. This does not impact any of the conclusions of the article. The corrected version of Fig. 4 is shown in this notice.

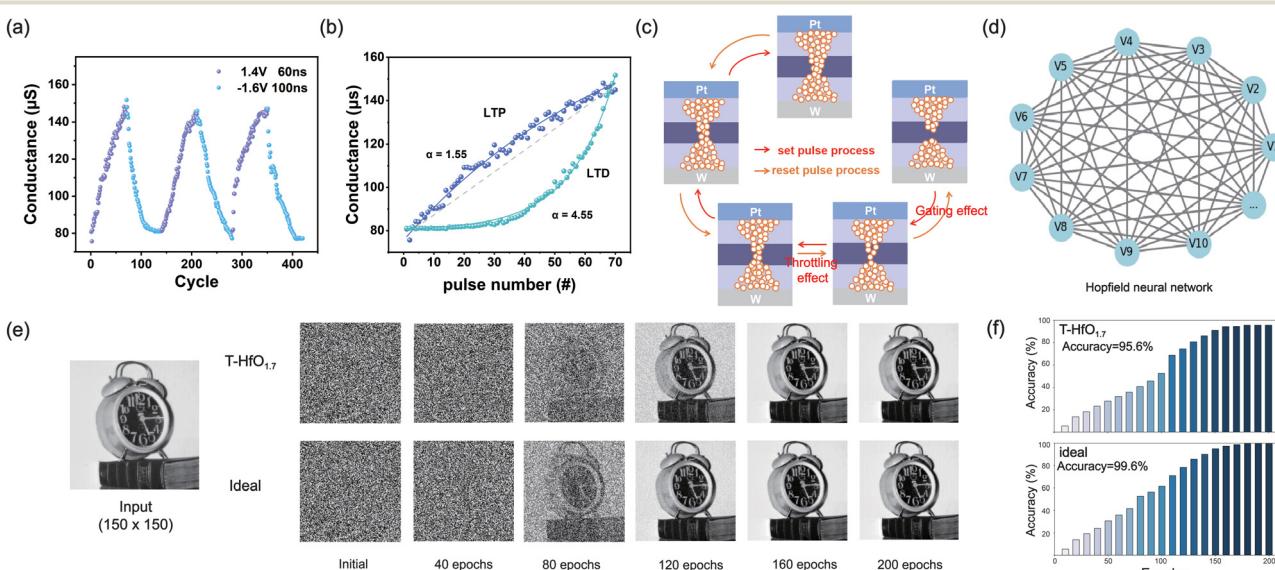


Fig. 4 (a) Cycle-to-cycle conductance evolution. (b) LTP/LTD process linearity fitting graph. (c) V_O migration diagram in the CFs during LTP/LTD. (d) Structure of the HNN. (e) Alarm clock images display process during 200 weight updates in HNN learning with the T-HfO_{1.7} and the device with ideal linearity. (f) The learning accuracy for the HNN.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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